

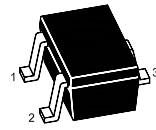
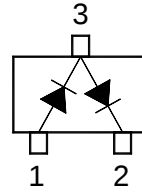
# RB706F-40

## Silicon Epitaxial Schottky Barrier Diode

For low current rectification

### Features

- High reliability
- Low reverse current



SOT-323 Plastic Package  
Marking Code: ZA

### Absolute Maximum Ratings ( $T_a = 25\text{ }^{\circ}\text{C}$ )

| Parameter                                          | Symbol      | Value         | Unit               |
|----------------------------------------------------|-------------|---------------|--------------------|
| Repetitive Peak Reverse Voltage                    | $V_{RM}$    | 45            | V                  |
| Reverse Voltage                                    | $V_R$       | 40            | V                  |
| Average Forward Rectified Current                  | $I_{F(AV)}$ | 30            | mA                 |
| Peak Forward Surge Current ( $t = 8.3\text{ ms}$ ) | $I_{FSM}$   | 200           | mA                 |
| Junction Temperature                               | $T_j$       | 125           | $^{\circ}\text{C}$ |
| Storage Temperature Range                          | $T_{stg}$   | - 55 to + 125 | $^{\circ}\text{C}$ |

### Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

| Parameter                                                                   | Symbol      | Min. | Typ. | Max. | Unit          |
|-----------------------------------------------------------------------------|-------------|------|------|------|---------------|
| Forward Voltage<br>at $I_F = 1\text{ mA}$                                   | $V_F$       | -    | -    | 0.37 | V             |
| Reverse Current<br>at $V_R = 10\text{ V}$                                   | $I_R$       | -    | -    | 1    | $\mu\text{A}$ |
| Reverse Breakdown Voltage<br>at $I_R = 10\text{ }\mu\text{A}$               | $V_{(BR)R}$ | 45   | -    | -    | V             |
| Capacitance between Terminals<br>at $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$ | $C_T$       | -    | 2    | -    | pF            |

